

SILICON PNP TRANSISTOR EPITAXIAL PLANAR TYPE (PCT PROCESS)

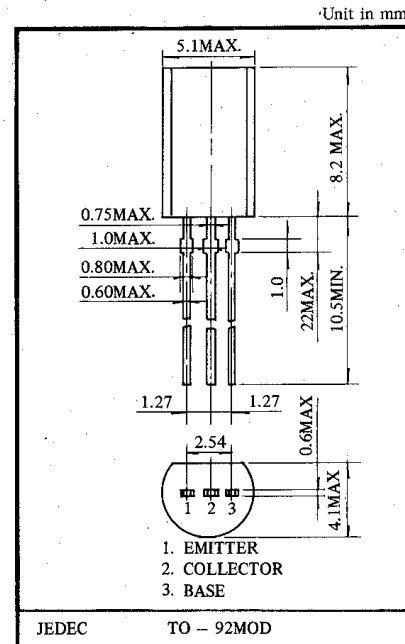
KTA817A

APPLICATIONS

- Driver Stage Amplifier Applications.
- Voltage Amplifier Applications.

FEATURES

- Complementary to KTC1627A.
- Driver Stage Application of 30 to 35 Watts Amplifiers.



■ MAXIMUM RATINGS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	-80	V
Collector-Emitter Voltage	V_{CE0}	-80	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-400	mA
Emitter Current	I_E	400	mA
Collector Dissipation	P_C	800	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55~150	°C

■ ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cutoff Current	I_{CB0}	$V_{CB} = -50V, I_E = 0$	—	—	-100	nA
Emitter Cutoff Current	I_{EB0}	$V_{EB} = -5V, I_C = 0$	—	—	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CE0}$	$I_C = -5mA$	-80	—	—	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -2V, I_C = -50mA$	70	—	240	
	$h_{FE(2)}$	$V_{CE} = -2V, I_C = -200mA$	40	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(Sat)}$	$I_C = -200mA, I_B = -20mA$	—	—	-0.4	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -2V, I_C = -5mA$	-0.55	—	-0.8	V
Transition Frequency	f_T	$V_{CE} = -10V, I_C = -10mA$	—	100	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	14	—	pF

■ NOTE: According to $h_{FE(1)}$, Classified as follows.

0	70-140	Y	120-240
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